Group 28 Resistor

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Introduction and Physical Properties

1) Cell Description

This report will detail the simulation of an inverter using a resistive load. The value of the load was chosen to emulated the behavior observed by using an enhancement load nFET inverter. The benefits or drawbacks of this configuration will be explored in this report.

2) Cell Symbol

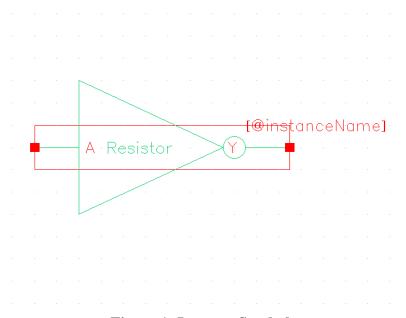


Figure 1: Inverter Symbol

Cell Truth Table

Cell Truth Table				
Cell Inputs {A} Cell Outputs {Y}				
0	1			
1	0			

3) Cell Schematic Diagram

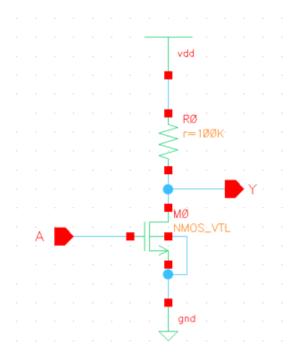


Figure 2: Inverter with Resistive Load

4,5) Cell Layout Diagram and Dimensions

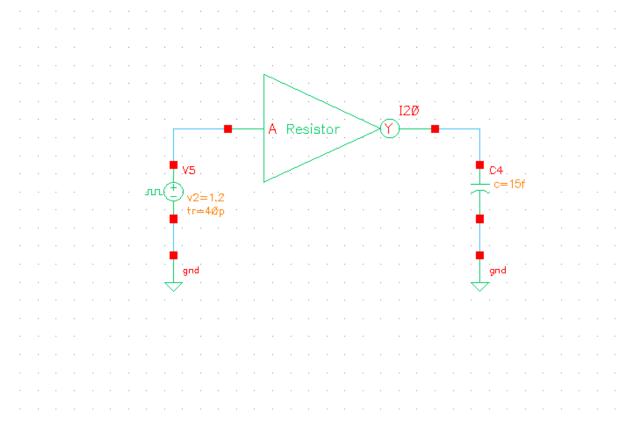


Figure 3: Inverter with Resistive Load Schematic

Transistor Dimensions						
Transistor Instance Number	Length (nm)	Width (nm)				
M0	90	50				

Performance Analysis

6,7) Rise and Fall Times

In the rise time and fall time table below, please ONLY fill in data for Output Load (Fox) = 4 and you do NOT need to fill in the data for Output load (Fox) of 0, 1, 2, 8 and can leave them blank.

Input X: Output Rise Time Data t _r (ns)							
Input rise/fall time		Output Load (Fox)					
(ns)	0	0 1 2 4 8					
0.04				1.915 ns			

Stack Input Combination: Replace with Boolean Product

Stack input combination neplace with 2001can rounds				
S, Input X: Output Fall Time Data t _f (ns)				
	Output Load (Fox)			

S, Input X: Output Fall Time Data t _f (ns)						
Input rise/fall time (ns)	0	1	2	4	8	
0.04				114.8 ps		

Stack Input Combination: Replace with Boolean Product

8,9) Propagation Delays

In the propagation delay tables below, please ONLY fill in data for Output Load (Fox) = 4 and you do NOT need to fill in the data for Output load (Fox) of 0, 1, 2, 8 and can leave them blank.

Data Worst Case Low to High Propagation Delay Data tplh (ns)							
Input rise/fall time	Output Load (Fox)						
(ns)	0	0 1 2 4 8					
0.04				957.891 ps			

Worse Case Input Combination: Replace with Boolean Product

Data Worst Case High to Low Propagation Delay Data t _{phl} (ns)							
Input rise/fall time		Output Load (Fox)					
(ns)	0	0 1 2 4 8					
0.04				91.141ps			

Worse Case Input Combination: Replace with Boolean Product

10, 11) Prepare two additional tables (shown below) comparing the performance of the six inverters.

DC Analysis

Туре	V _{IH_DC}	V _{IL_DC}	$V_{\text{OH_DC}}$	$V_{\text{ol_DC}}$
CMOS	613.3	369.374mV	1.129 V	53.0749
	mV			mV
CMOS_Wide	614.032	369.597	1.12876	53.98402
	mV	mV	V	mV
Enhancement mode NFET	624.679	344.751	508.4854	117.3766
	mV	mV	mV	mV
Enhancement mode NFET_Long	550.588	270.727	528.8089	66.04702
	mV	mV	mV	mV
Resistive load (100k Ohms)	612.429	276.79 mV	1.12942	88.8312
	mV		V	mV
Resistive load_long (350k Ohms)	527.1055	218.764	527.105	46.21169
	mV	mV	mV	mV

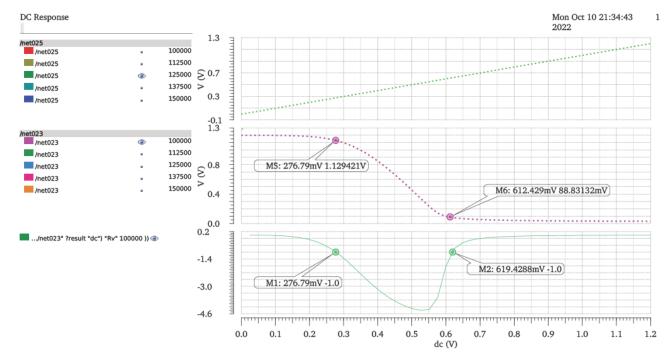


Figure 4: Inverter with Resistive Load DC Simulation

Transient Analysis

Туре	tp₅	tpы	t,	t _f
CMOS	275.31 ps	92.428 ps	397.4 ps	115.4 ps
CMOS_Wide	70.8488 ps	27.66 ps	94.62 ps	29.35 ps
Enhancement mode NFET	352.924 ps	60.862 ps	1.224 ns	73.24 ns
Enhancement mode NFET_Long	836.513 ps	55.4595 ps	2.017 ns	75.0 ps
Resistive load	957.891 ps	91.141ps	1.915 ns	114,8 ps
Resistive load_long	2.03 ns	61.69 ps	2.816 ns	84.26 ps

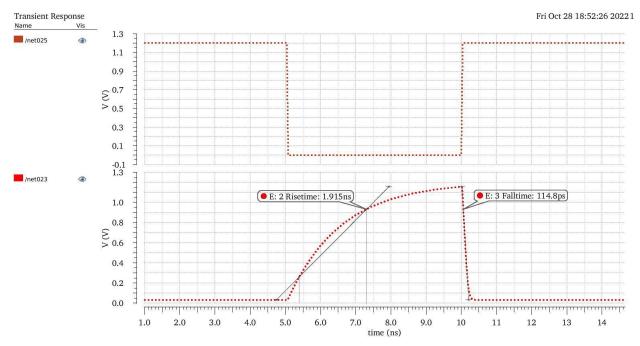


Figure 5: Inverter with Resistive Load Transient Fall/Rise time

Introduction and Physical Properties

1) Cell Description

This report will detail the simulation of an inverter using a resistive load. The value of the load was chosen to emulated the behavior observed by using an enhancement load nFET inverter in the long configuration. The benefits or drawbacks of this configuration will be explored in this report.

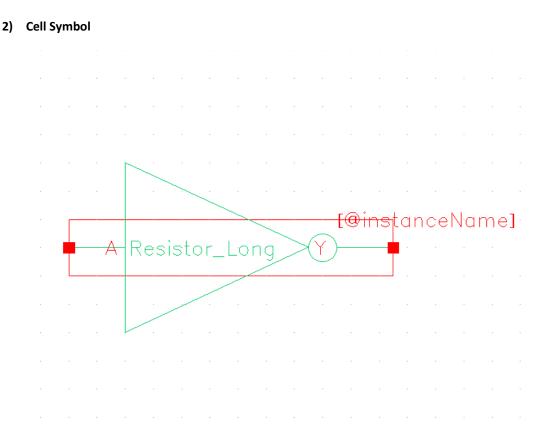


Figure 6: Inverter Symbol

Cell Truth Table

Cell Truth Table					
Cell Inputs {A} Cell Outputs {Y}					
0	1				
1	0				

3) Cell Schematic Diagram

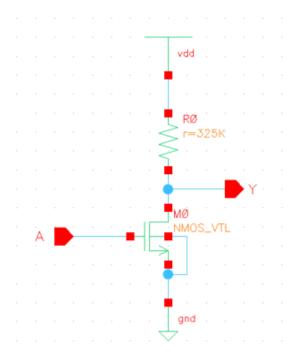


Figure 7: Inverter with Resistive Load

4,5) Cell Layout Diagram and Dimensions

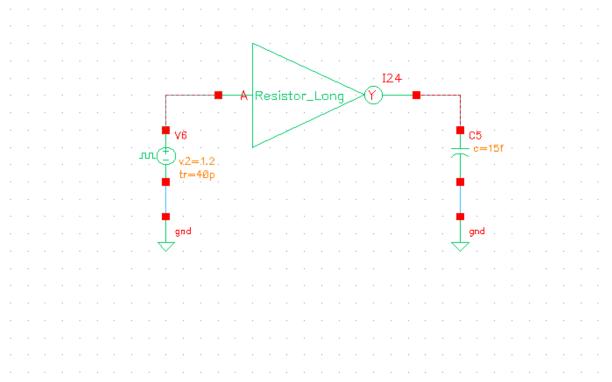


Figure 8: Inverter with Resistive Load Schematic (Long)

Transistor Dimensions						
Transistor Instance Number Length (nm) Width (nm)						
M0	90	50				

Performance Analysis

6,7) Rise and Fall Times

In the rise time and fall time table below, please ONLY fill in data for Output Load (Fox) = 4 and you do NOT need to fill in the data for Output load (Fox) of 0, 1, 2, 8 and can leave them blank.

Input X: Output Rise Time Data t _r (ns)							
Input rise/fall time		Output Load (Fox)					
(ns)	0	0 1 2 4 8					
0.04	Х	Х	Х	2.816 ns	Х		

Stack Input Combination: Replace with Boolean Product

Stack input combination. Replace with boolean Froduct				
S, Input X: Output Fall Time Data t _f (ns)				
	Output Load (Fox)			

S, Input X: Output Fall Time Data t _f (ns)						
Input rise/fall time (ns) 0 1 2 4 8						
0.04	Х	Х	Х	84.26 ps	Х	

Stack Input Combination: Replace with Boolean Product

8,9) Propagation Delays

In the propagation delay tables below, please ONLY fill in data for Output Load (Fox) = 4 and you do NOT need to fill in the data for Output load (Fox) of 0, 1, 2, 8 and can leave them blank.

Data Worst Case Low to High Propagation Delay Data tplh (ns)							
Input rise/fall time	Output Load (Fox)				Output Load (Fox)		
(ns)	0	1	2	4	8		
0.04	Х	Х	Х	2.03 ns	Х		

Worse Case Input Combination: Replace with Boolean Product

Data Worst Case High to Low Propagation Delay Data t _{phl} (ns)					
Input rise/fall time	Output Load (Fox)				
(ns)	0	1	2	4	8
0.04	Х	Х	Х	61.69 ps	X

Worse Case Input Combination: Replace with Boolean Product

10, 11) Prepare two additional tables (shown below) comparing the performance of the six inverters.

DC Analysis

Туре	V _{IH_DC}	V _{IL_DC}	$V_{\text{OH_DC}}$	$V_{\text{ol_DC}}$
CMOS	613.3	369.374mV	1.129 V	53.0749
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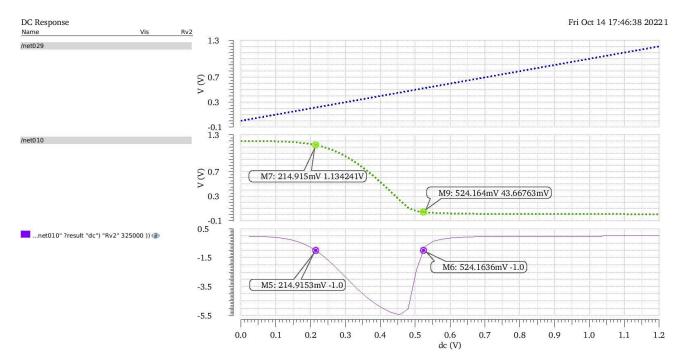


Figure 9: Inverter with Resistive Load DC Simulation

Transient Analysis

Туре	tp⊪	tpы	t r	t,
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CMOS_Wide	70.8488 ps	27.66 ps	94.62 ps	29.35 ps
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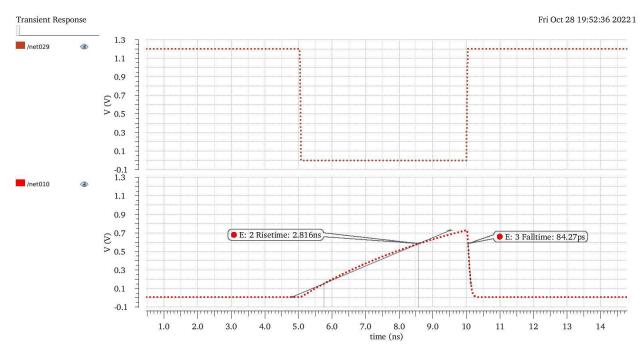


Figure 10: Inverter with Resistive Load Transient Fall/Rise time